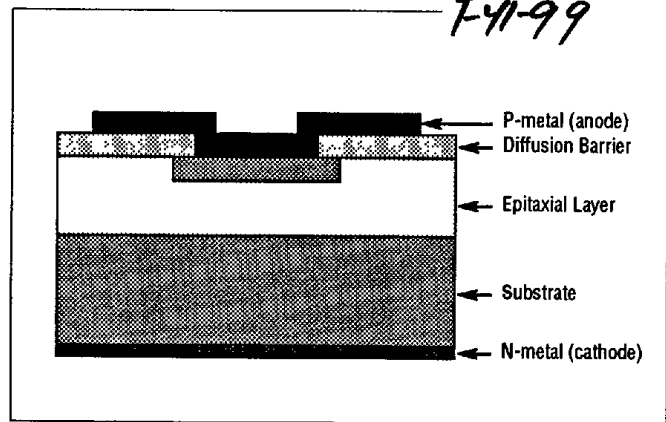
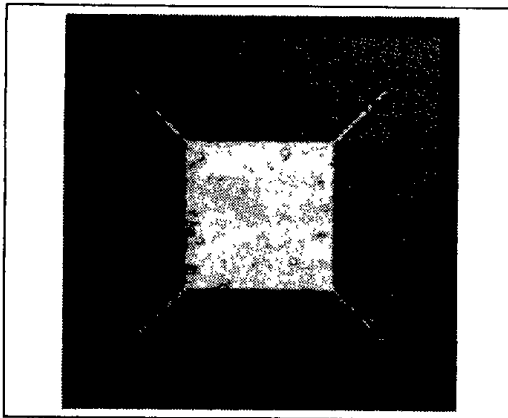


SIEMENS

**RP-12C
Mask-Diffused GaAsP LED**

PART NO. 2680-7075

Custom
Optoelectronic
Products



DESCRIPTION

Siemens RP-12C is a mask-diffused GaAsP light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for lamp and display applications.

MATERIAL

Epitaxial Layer: GaAs_{1-x}P_x : Te
 Substrate: GaAs : Si or GaAs : Te
 Metalizations: Anode Aluminum
 Cathode Gold-Germanium

Dimensions

(center to center): Height 0.012"
 Width 0.012"
 Thickness 0.010"

TYPICAL DEVICE PARAMETERS

Forward I-V Characteristics	V _{F3}	1.70 V	Ⓢ 20 mA
	V _{F2}	1.64 V	Ⓢ 10 mA
	V _{F1}	1.45 V	Ⓢ 100 μA
Reverse I-V Characteristics	V _{R1}	-25.0 V	Ⓢ -10 μA
Peak EL Wavelength	λ	655 nm	Ⓢ 20 mA
Spectral Half-Width	FWHM	40 nm	Ⓢ 20 mA
Luminous Intensity	LI	500 μCd	Ⓢ 10 mA